BT137B series E

GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope suitable for surface mounting, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

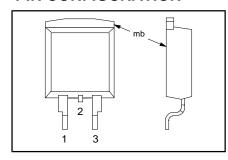
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	BT137B- Repetitive peak off-state	500E 500	600E 600	800E 800	V
I _{T(RMS)} I _{TSM}	voltages RMS on-state current Non-repetitive peak on-state current	8 65	8 65	8 65	A A

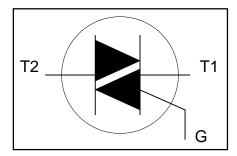
PINNING - SOT404

PIN	DESCRIPTION	
1	main terminal 1	
2	main terminal 2	
3	gate	
mb	main terminal 2	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge	-		8		А
		t = 20 ms	-		65 71		A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 16.7 ms t = 10 ms $I_{TM} = 12 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		71 21		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	- - -		50 50 50 10		A/μs A/μs A/μs A/μs
I _{GM} V _{GM}	Peak gate current Peak gate voltage Peak gate power	12- 9+	-		2 5 5		Ανμs Α V W
P _{GM} P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		.C .C

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle minimum footprint, FR4 board		- - 55	2.0 2.4 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G+	-	2.5	10	mΑ
		T2+ G-	-	4.0	10	mΑ
		T2- G-	-	5.0	10	mΑ
		T2- G+	-	11	25	mΑ
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
		T2+ G+	-	3.0	25	mA
		T2+ G-	-	14	35	mA
		T2- G-	-	3.0	25	mĄ
		T2- G+	-	4.0	35	mA
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	2.5	20	mΑ
V_{T}	On-state voltage	$I_T = 10 \text{ A}$	-	1.3	1.65	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	0.25	0.4		V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$, $T_j = 125 °C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	-	50	-	V/μs
t _{gt}	off-state voltage Gate controlled turn-on time	exponential waveform; gate open circuit $I_{TM} = 12 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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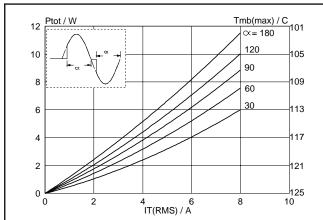


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

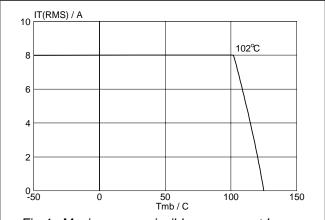


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

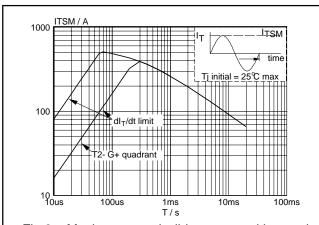


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

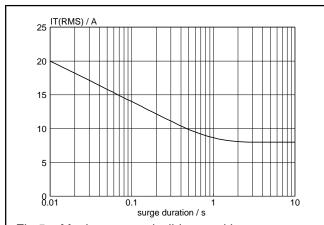


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 102$ °C.

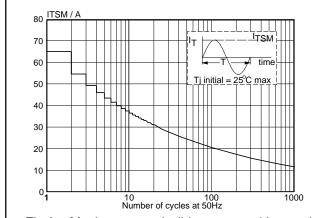


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

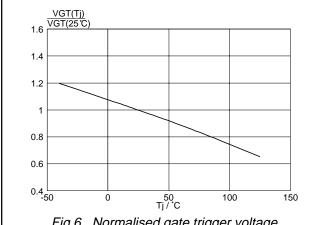
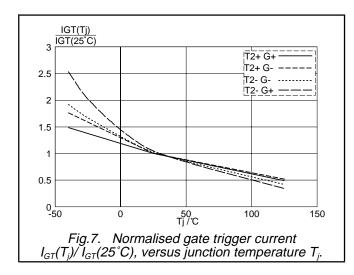
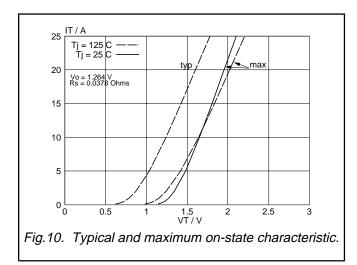
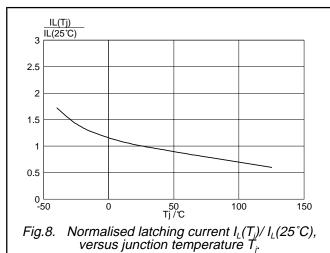


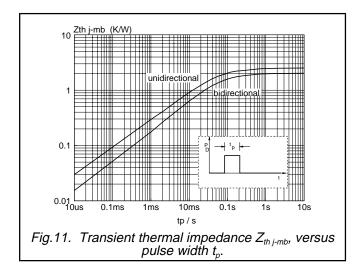
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

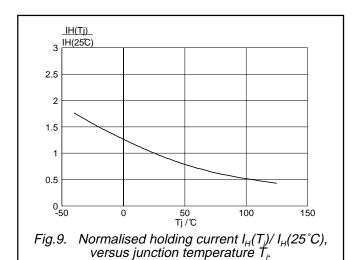
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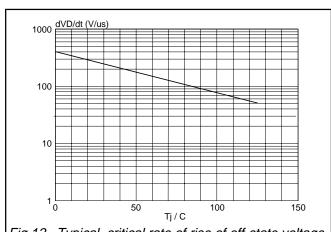
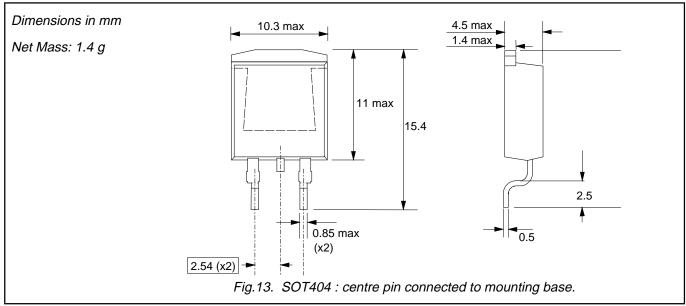


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

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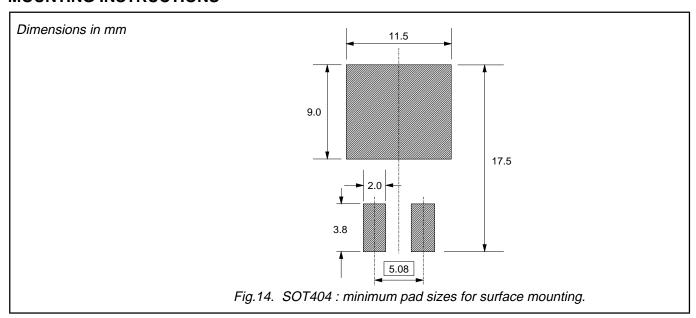
MECHANICAL DATA



Notes

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Triacs sensitive gate

BT137B series E

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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